

General Description

The WST3429 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent $R_{DS(on)}$ and gate charge for most of the small power switching and load switch applications.

The WST3429 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent $C_{dv/dt}$ effect decline
- Green Device Available

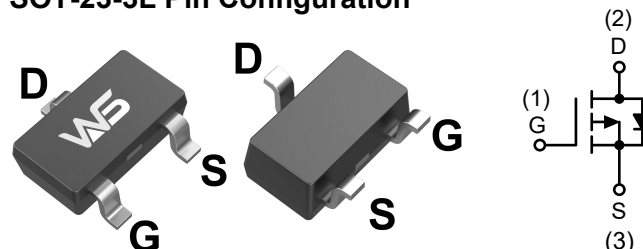
Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D
-20V	150mΩ	-2.3A

Applications

- High Frequency Point-of-Load Synchronous
Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 8	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-2.3	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-1.0	A
I_{DM}	Pulsed Drain Current ²	-10	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.014	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V$, $I_D=-1A$	---	150	185	$m\Omega$
		$V_{GS}=-2.5V$, $I_D=-1A$	---	170	285	
		$V_{GS}=-1.8V$, $I_D=-1A$	---	200	430	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-0.4	-0.7	-1.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.3	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-1A$	---	5.0	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-1A$	---	5.6	---	nC
Q_{gs}	Gate-Source Charge		---	1.21	---	
Q_{gd}	Gate-Drain Charge		---	2.46	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$ $I_D=-1A$	---	5.0	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	4.5	---	
T_f	Fall Time		---	21	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	357	---	pF
C_{oss}	Output Capacitance		---	72	---	
C_{rss}	Reverse Transfer Capacitance		---	61	---	

Diode Characteristics

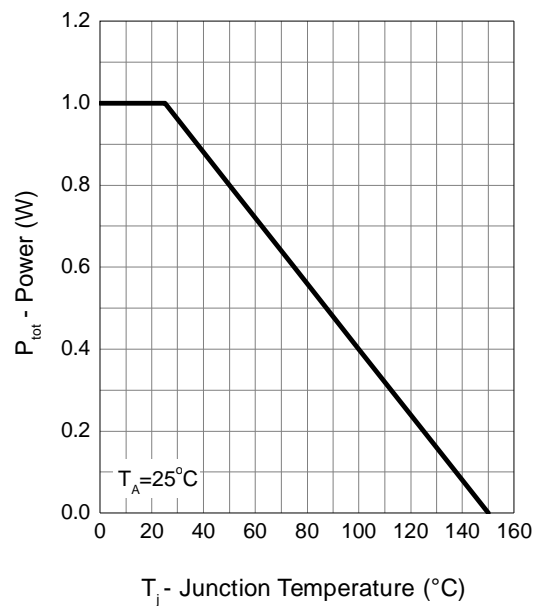
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-1	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-3	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-1A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	12	---	nS
Q_{rr}	Reverse Recovery Charge		---	6.0	---	nC

Note :

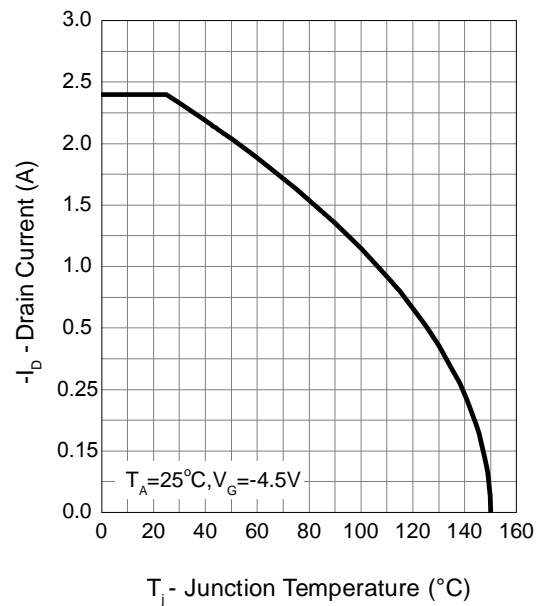
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, $t<10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Operating Characteristics

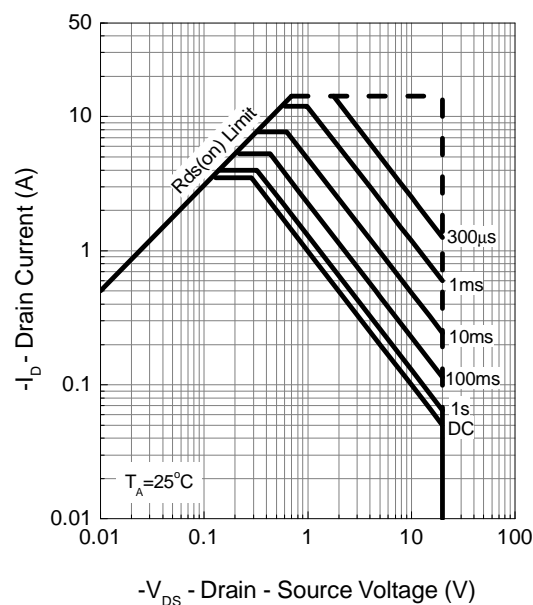
Power Dissipation



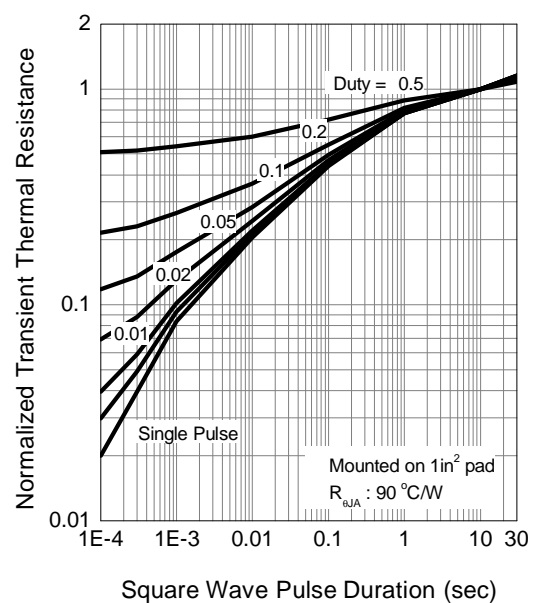
Drain Current



Safe Operation Area

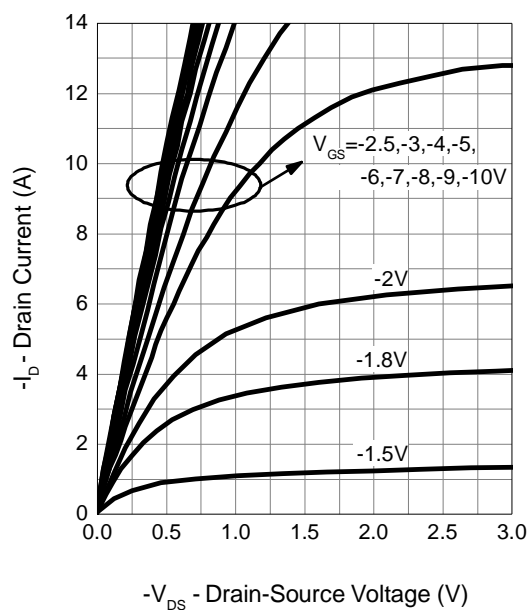


Thermal Transient Impedance

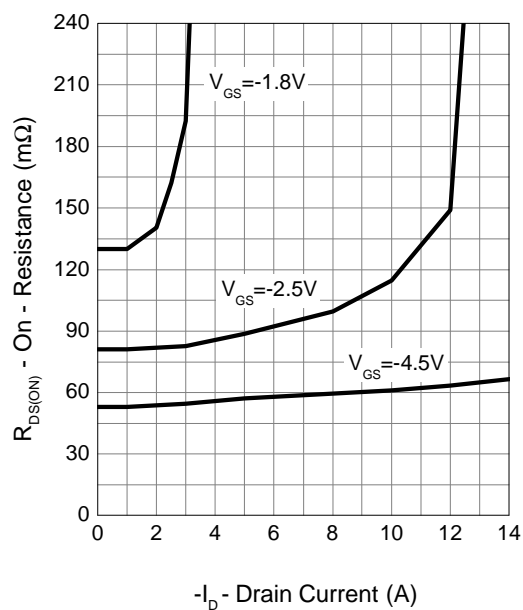


Typical Operating Characteristics

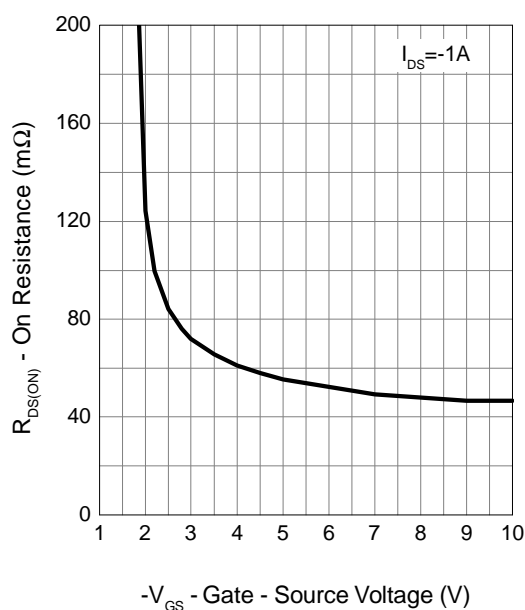
Output Characteristics



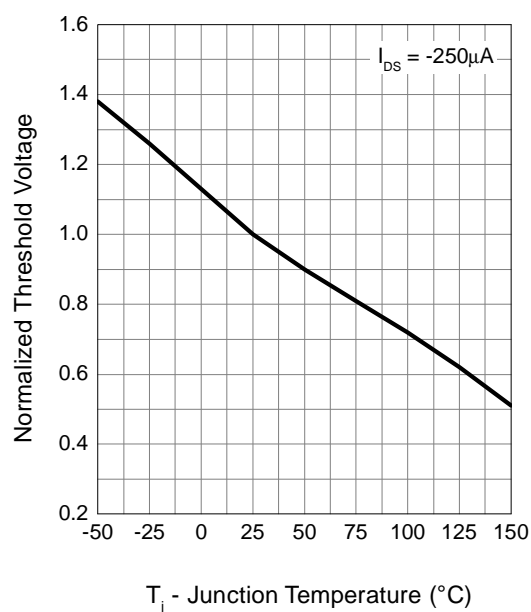
Drain-Source On Resistance



Gate-Source On Resistance

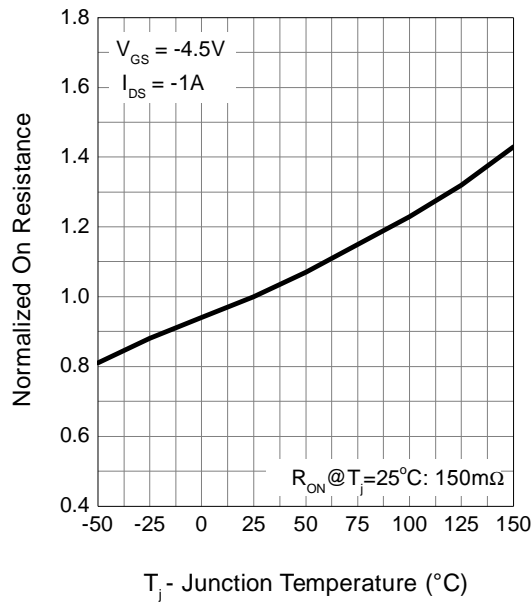


Gate Threshold Voltage

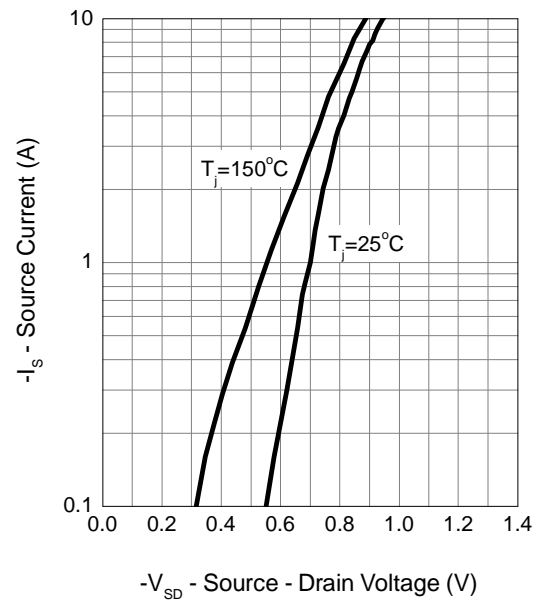


Typical Operating Characteristics

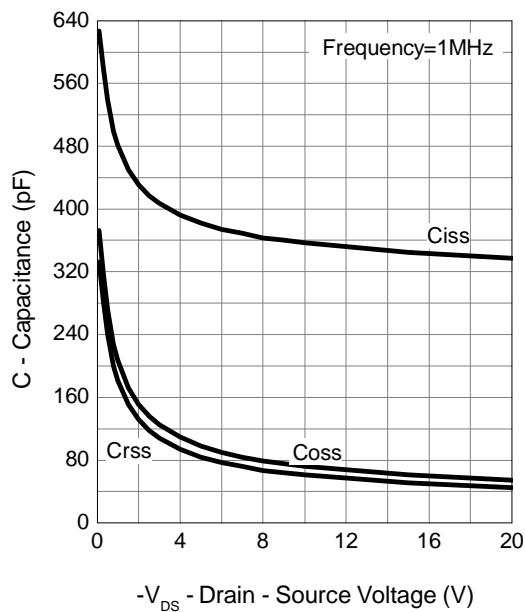
Drain-Source On Resistance



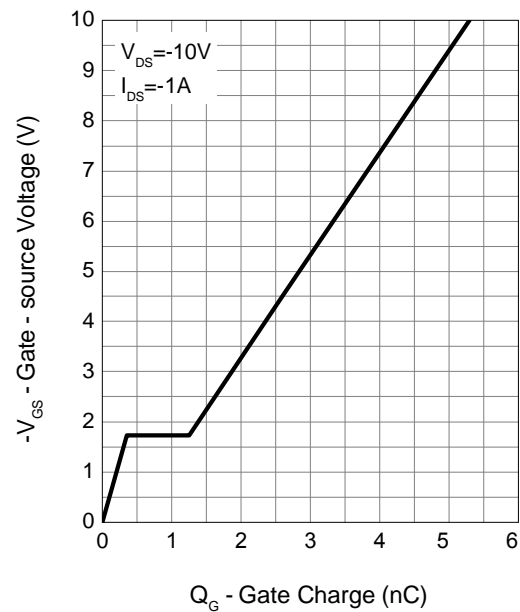
Source-Drain Diode Forward



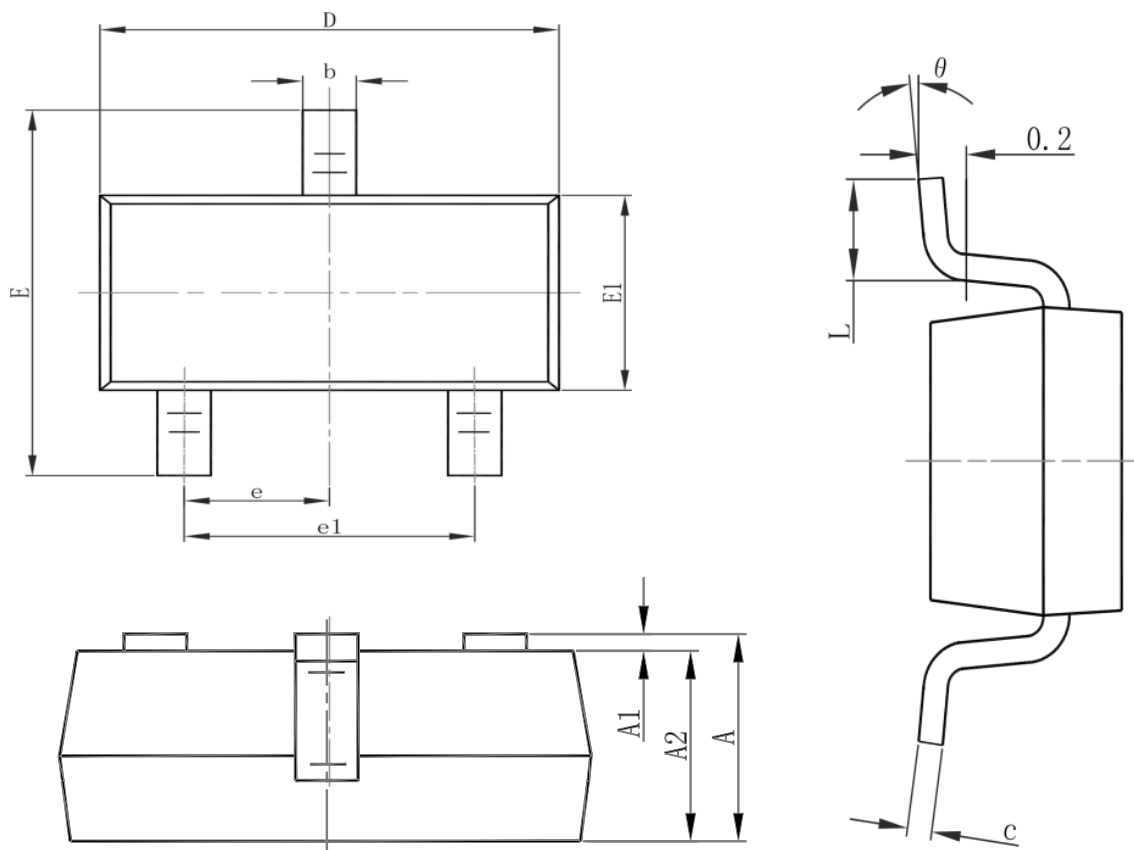
Capacitance



Gate Charge



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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